

isc Silicon NPN Power Transistor

2SC2562

DESCRIPTION

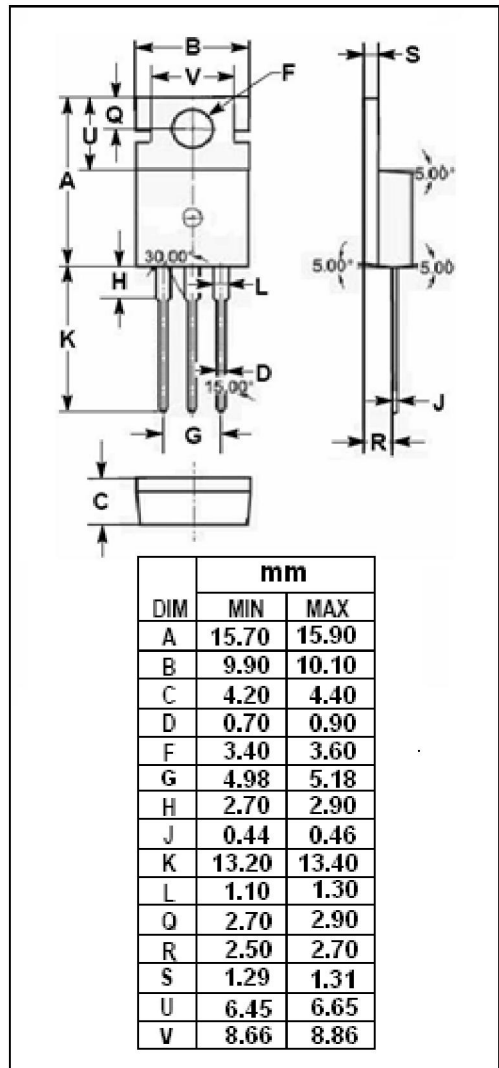
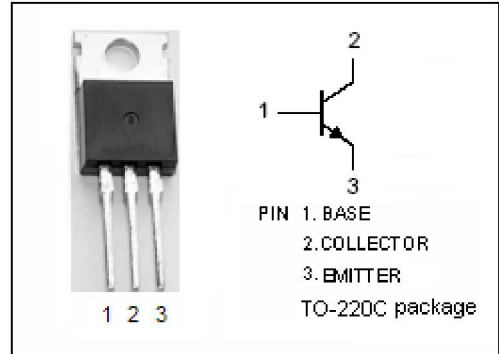
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.4(V)(Max) @ I_C = 3A$
- High Switching Speed
- Complement to Type 2SA1012

APPLICATIONS

- Designed for high current switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_B	Base Current- Continuous	1	A
P_C	Total Power Dissipation @ $T_C=25^{\circ}C$	25	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SC2562****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA ; I _B = 0	50			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.15A			0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3A; I _B = 0.15A			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 50V ; I _E = 0			1	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			1	μ A
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 1V	70		240	
h _{FE-2}	DC Current Gain	I _C = 3A ; V _{CE} = 1V	30			
f _T	Current-Gain—Bandwidth Product	I _C = 1A ; V _{CE} = 4V		120		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1MHz		80		pF

Switching Times

t _{on}	Turn-on Time	I _C = 3A, R _L = 10Ω, I _{B1} = -I _{B2} = 0.15A, V _{CC} = 30V		0.1		μ s
t _{stg}	Storage Time			1.0		μ s
t _f	Fall Time			0.1		μ s

◆ h_{FE-1} Classifications

O	Y
70-140	120-240